★ 100% EAS Guaranteed
★ Green Device Available
★ Super Low Gate Charge
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

Product Summary

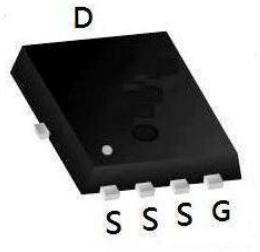
BVDSS	RDSON	ID
20V	6.3 mΩ	40A

Description

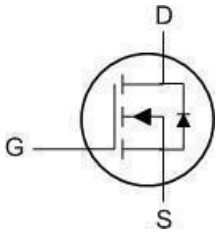
The ZX 40N02 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The ZX 40N02 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

PDFN3×3-8L Pin Configuration



pin assignment



Schematic diagram

Package Marking and Ordering Information

Product	Package	Marking	Packing	Min Unit Quantity
ZX 40N02	PDFN3*3-8L	*	5000PCS/Reel	5000PCS

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS}@ 10V[1]	40	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS}@ 10V[1]	23	A
I_{DM}	Pulsed Drain Current[2]	210	A
EAS	Single Pulse Avalanche Energy[3]	36	mJ
I_{AS}	Avalanche Current	21	A
P_D@T_C=25℃	Total Power Dissipation[4]	15	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	4.8	℃/W

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V, V_{GS}=0V,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}=±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.4	0.7	1.1	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}=4.5V, I_D=25A	-	6.3	8.0	mΩ
		V_{GS}=2.5V, I_D=10A	-	8.8	13	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=10V, V_{GS}=0V, f=1.0MHz	-	1458	-	pF
C_{oss}	Output Capacitance		-	238	-	pF
C_{rss}	Reverse Transfer Capacitance		-	212	-	pF
Q_g	Total Gate Charge	V_{DS}=10V, I_D=25A, V_{GS}=4.5V	-	19	-	nC
Q_{gs}	Gate-Source Charge		-	3	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	6.4	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=10V, I_D=10A, R_{GEN}=3Ω, V_{GS}=4.5V	-	10	-	ns
t_r	Turn-on Rise Time		-	21	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	39	-	ns
t_f	Turn-off Fall Time		-	19	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	40	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	200	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=30A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	IF=20A,dI/dt=100A/μs	-	25	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	20	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25℃, V_{DD}=10V, V_G=4.5V, L=0.5mH, R_G=25Ω, I_{AS}=12A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Characteristics

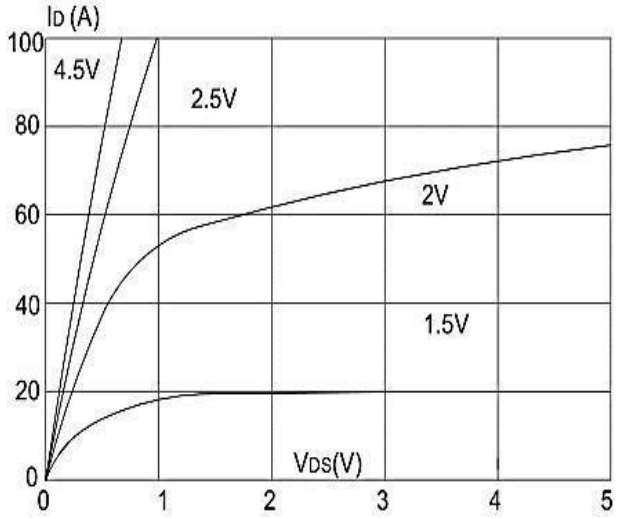


Figure1: Output Characteristics

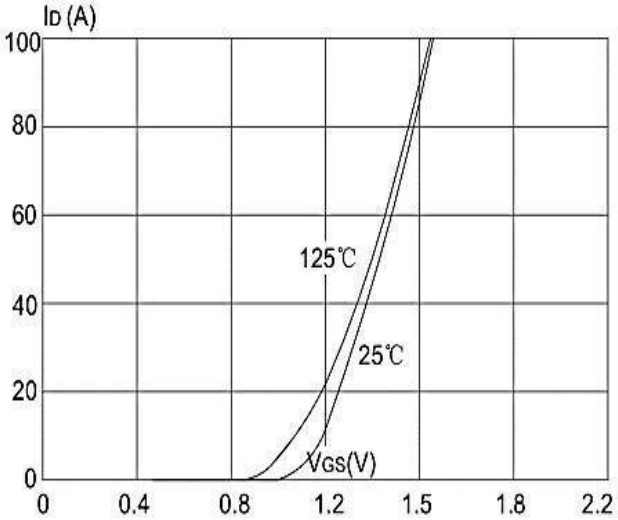


Figure 2: Typical Transfer Characteristics

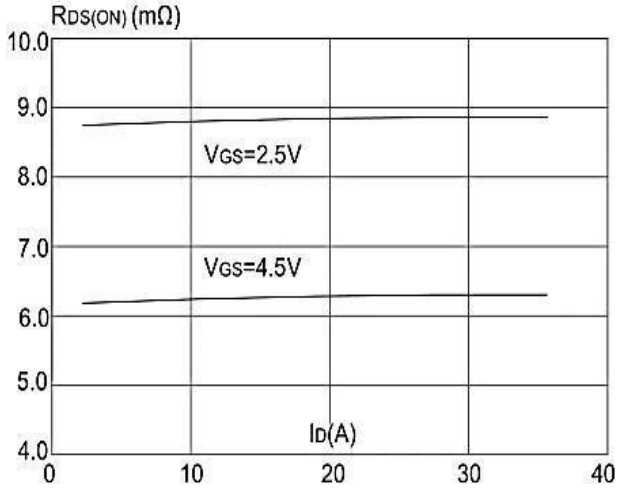


Figure 3:On-resistance vs. Drain Current

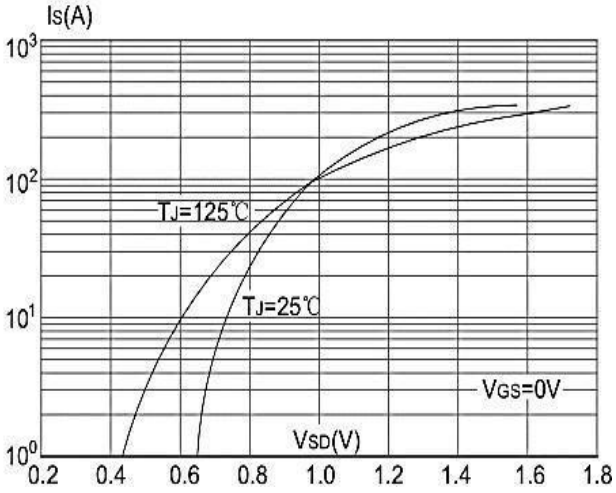


Figure 4: Body Diode Characteristics

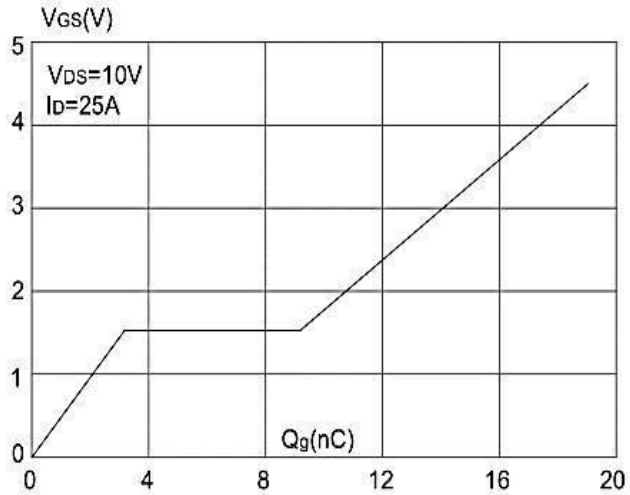


Figure 5: Gate Charge Characteristics

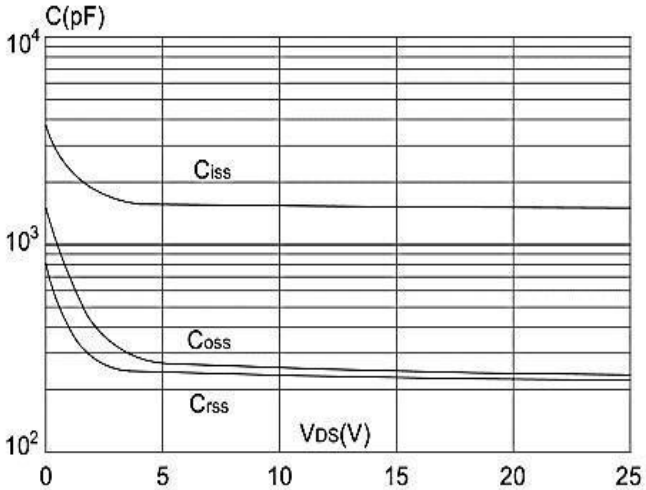


Figure 6: Capacitance Characteristics

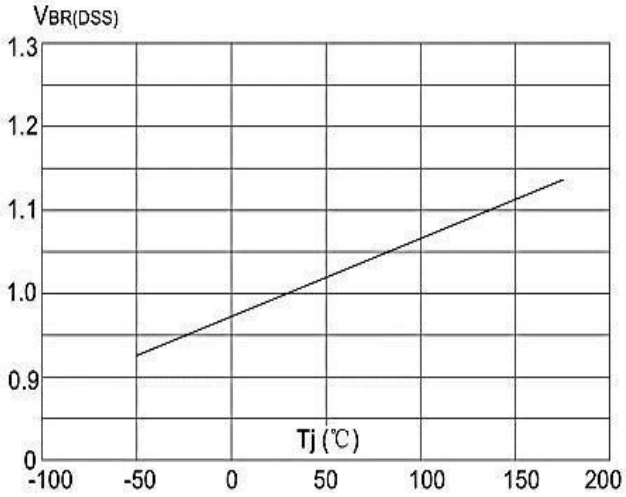


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

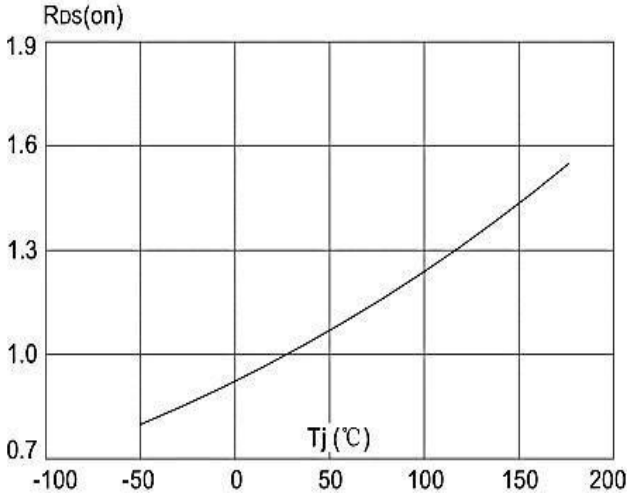


Figure 8: Normalized on Resistance vs Junction Temperature

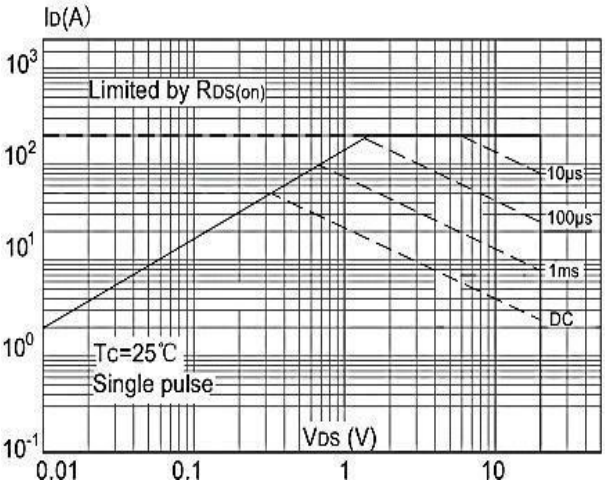


Figure 9: Maximum Safe Operating Area vs. Case Temperature

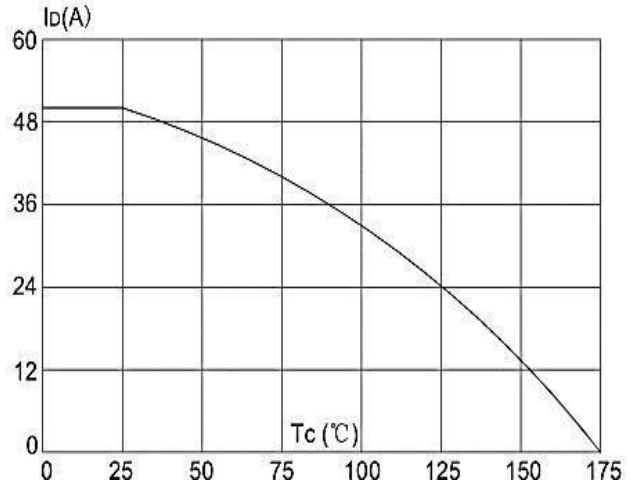


Figure 10: Maximum Continuous Drain Current

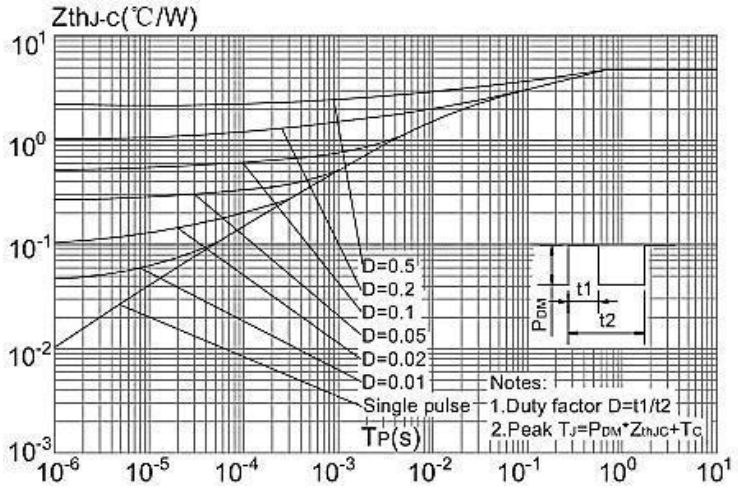
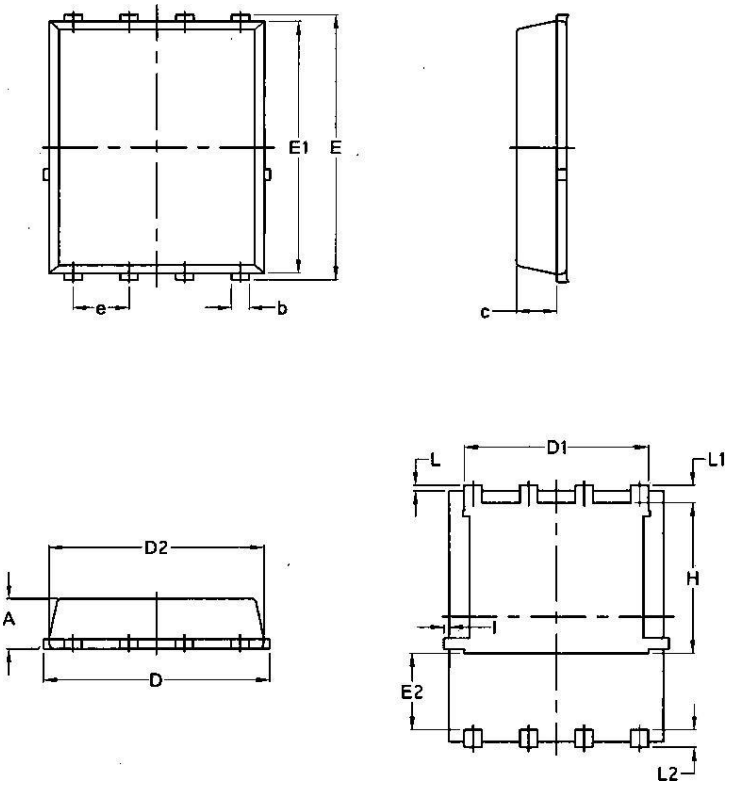


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

Package Mechanical Data-PDFN3333-8L-JQ Single



COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.80	0.90
A1	0.00	0.03	0.05
b	0.24	0.30	0.35
c	0.10	0.15	0.20
D	3.25	3.32	3.40
D1	3.05	3.15	3.25
D2	2.40	2.50	2.60
E	3.00	3.10	3.20
E1	1.35	1.45	1.55
e	0.65 BSC.		
H	3.20	3.30	3.40
L	0.30	0.40	0.50
L1	0.10	0.15	0.20
L2	1.13 REF.		